



JCT855Z 55A SCR

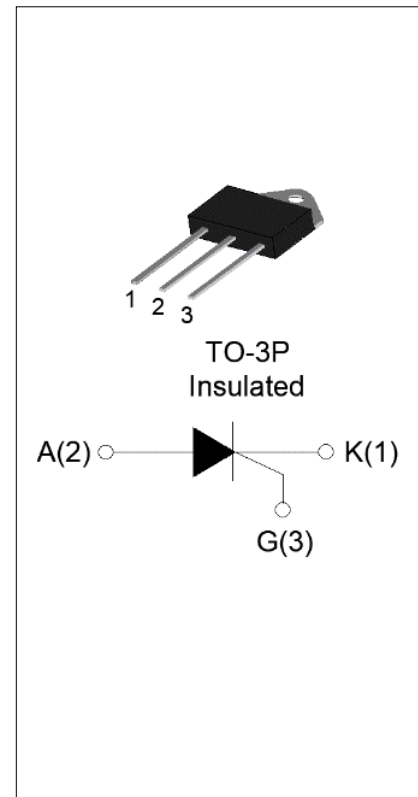
Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT855Z SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT855Z provides a rated insulation voltage of 2500 V_{RMS} , complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	55	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	10-50	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 60^{\circ}C$)	$I_{T(AV)}$	35	A
RMS on-state current ($T_c \leq 60^{\circ}C$)	$I_{T(RMS)}$	55	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^{\circ}C$)	I_{TSM}	700	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^{\circ}C$)		750	
I^2t value for fusing ($t_p=10ms, T_j=25^{\circ}C$)	I^2t	2450	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^{\circ}C$)	di/dt	200	$A/\mu s$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	10	-	50	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3k\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	120	mA
I_H	$I_T=500mA$	-	-	100	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125^\circ C$	1500	-	-	V/ μs
t_{on}	$I_G=50mA$ $I_A=500mA$ $I_R=50mA$ $T_j=25^\circ C$	-	4	-	μs
t_{off}		-	130	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=80A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.76	V
R_D	Dynamic resistance	$T_j=125^\circ C$	8.5	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	9	μA
I_{RRM}		$T_j=125^\circ C$	5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	0.85	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	55	$^\circ C/W$

ORDERING INFORMATION

<u>J</u>	<u>CT</u>	<u>8</u>	<u>55</u>	<u>Z</u>
JieJie Microelectronics Co., Ltd.	SCRs			Z:TO-3P(Ins)
	8: $V_{DRM}/V_{RRM} \geq 800V$		IT(RMS):55A	

MARKING

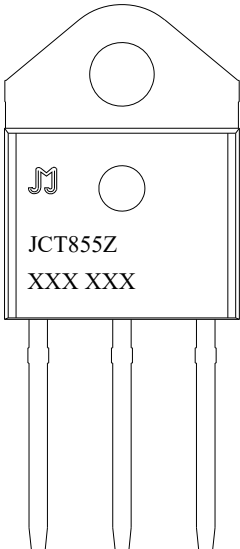
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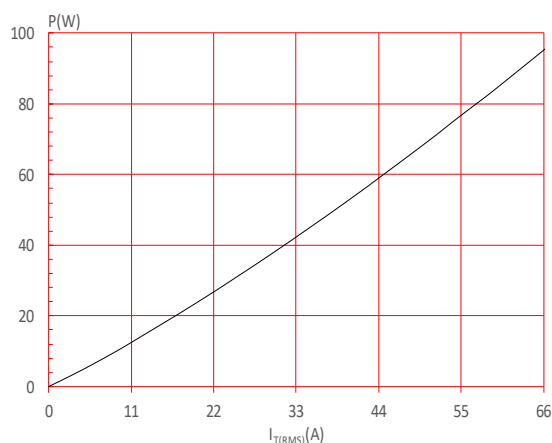
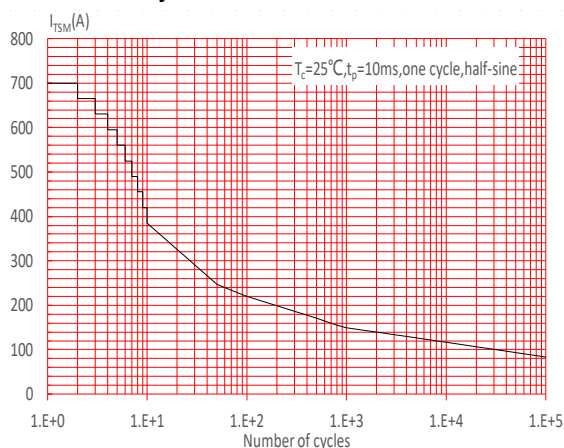
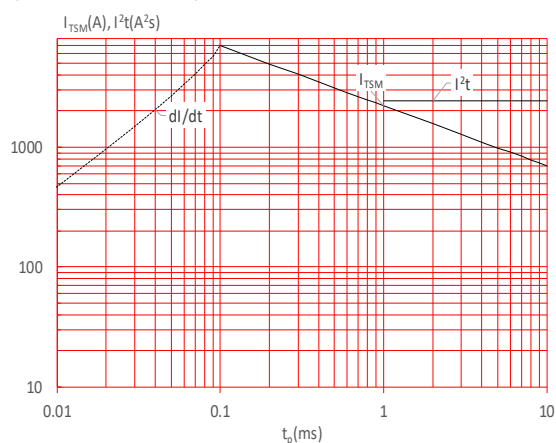
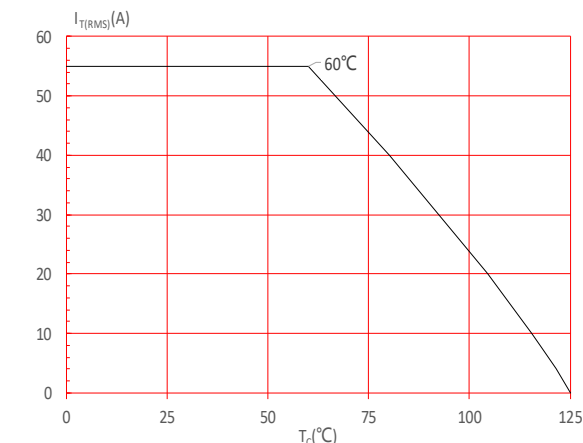
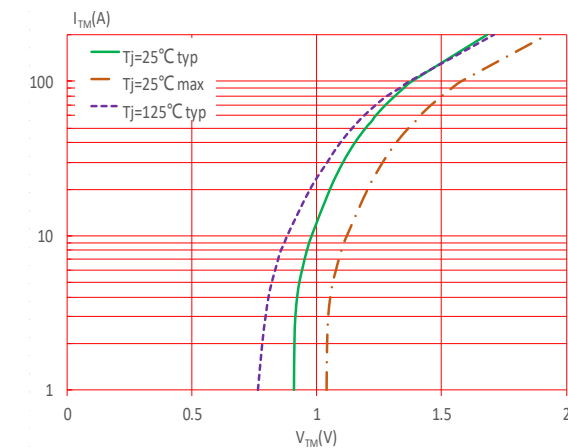
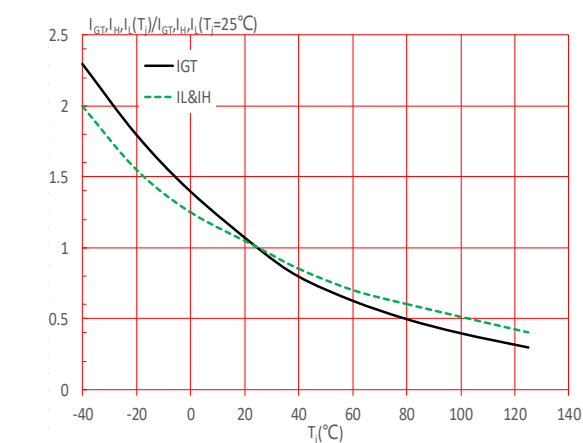
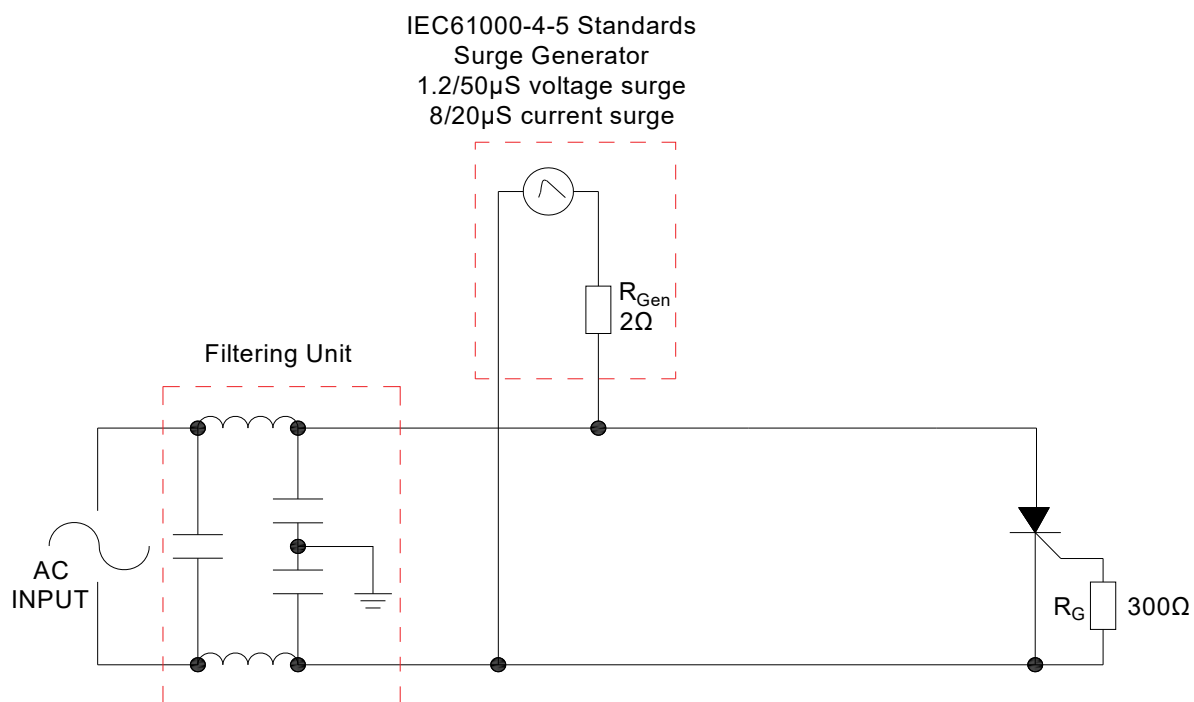
FIG.1: Maximum power dissipation versus RMS on-state current**FIG.3:** Surge peak on-state current versus number of cycles**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 200\text{A}/\mu\text{s}$)**FIG.2:** RMS on-state current versus case temperature**FIG.4:** On-state characteristics**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie Microelectronics

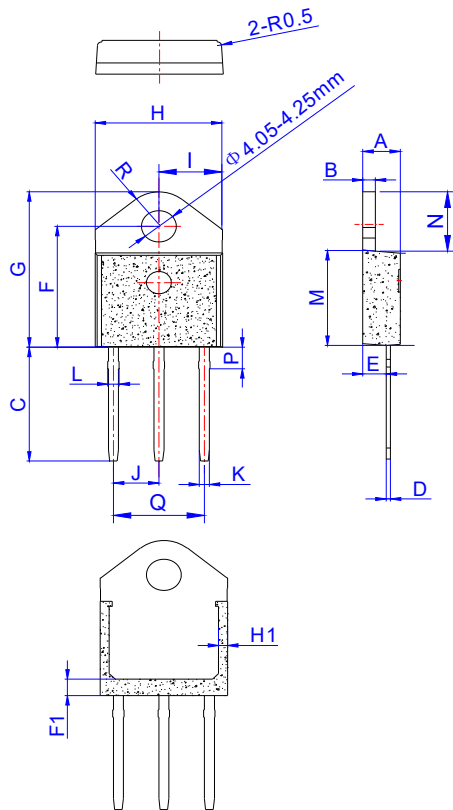
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT855Z	800	10-50	TO-3P(Ins)	30	Tube

Document Revision History

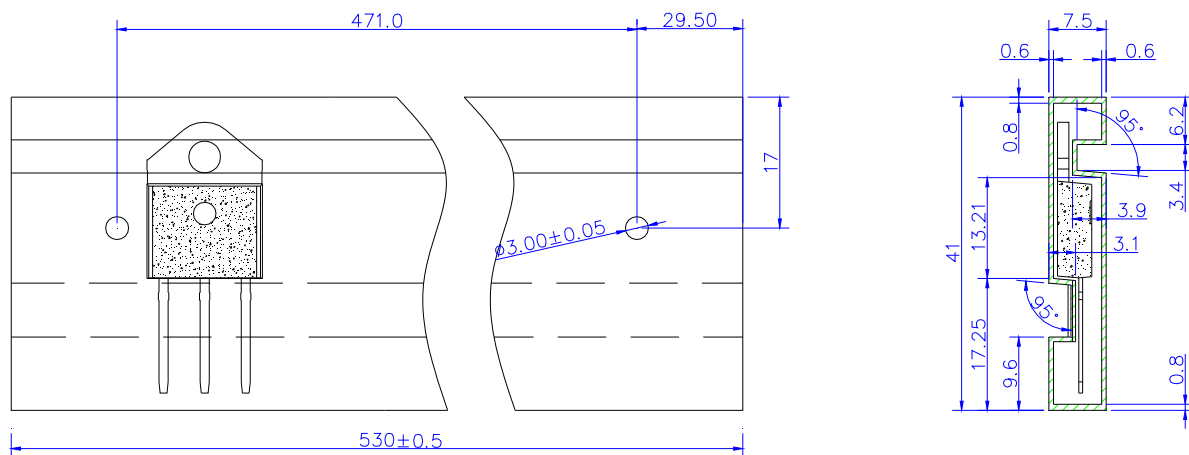
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
F1	2.45		2.85	0.096		0.112
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
H1	1.10		1.50	0.043		0.059
I	7.25		7.65	0.285		0.301
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
N	7.80		8.20	0.307		0.323
P	2.80		3.00	0.110		0.118
Q	10.70		11.10	0.421		0.437
R		4.35			0.171	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250

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